

Band Switching Diode

- **Applications**

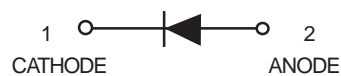
High frequency switching

- **Features**

- 1) Small surface mounting type.
- 2) High reliability.

- **Construction**

Silicon epitaxial planar



L1SS356T1



Driver Marking

L1SS356T1 = B

Absolute maximum ratings (T_A=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V _R	35	V
DC forward current	I _F	100	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55~+125	°C

Electrical characteristics (T_A=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F	–	–	1.0	V	I _F =10mA
Reverse current	I _R	–	–	10	nA	V _R =25V
Capacitance between terminals	C _T	–	–	1.2	pF	V _R =6V, f =1MHz
Forward operating resistance	r _F	–	–	0.9	Ω	I _F =2mA, f =100MHz

Electrical characteristic curves

($T_A=25^\circ\text{C}$)

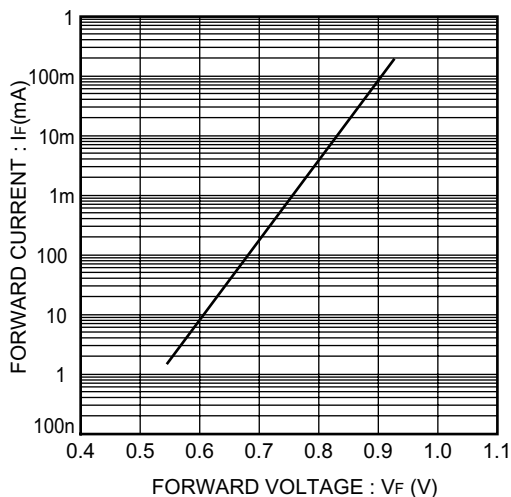


Fig. 1 Forward characteristics

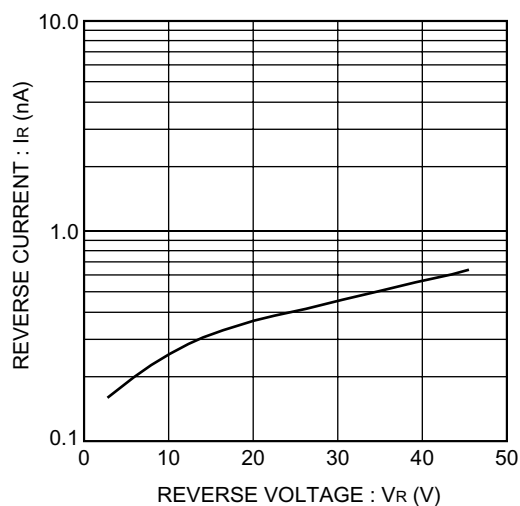


Fig. 2 Reverse characteristics

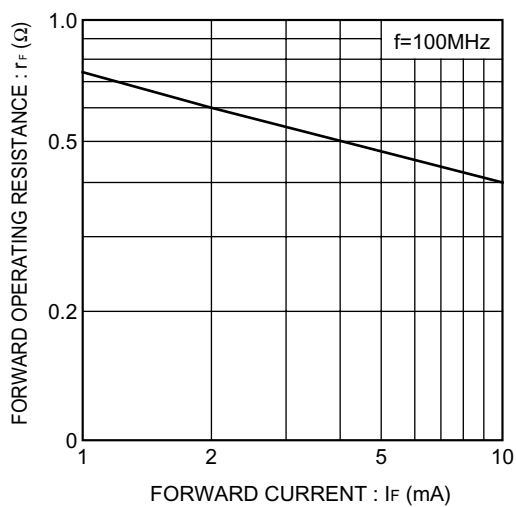


Fig. 4 Forward operating resistance characteristics

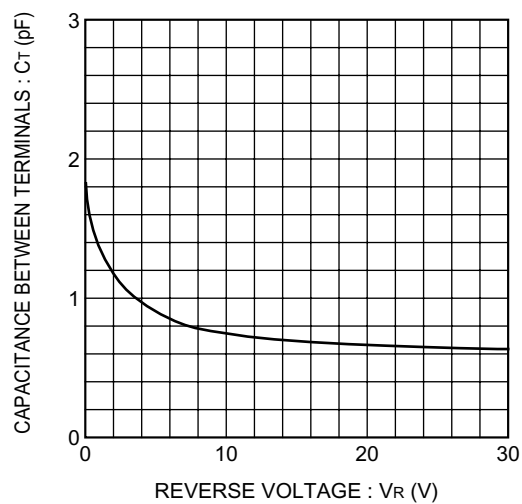


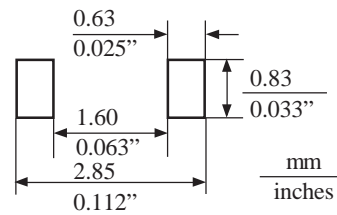
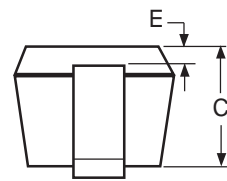
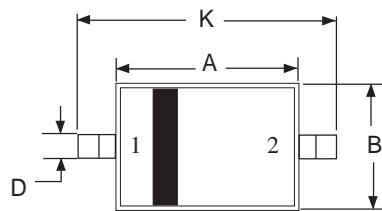
Fig. 3 Capacitance between terminals characteristics

L1SS356T1

PACKAGE DIMENSIONS
SOD-323
PLASTIC PACKAGE
CASE 477-02
ISSUE B



SOD-323



NOTES:

1. CONTROLLING DIMENSION: MILLIMETERS
2. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.

DIN	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.60	1.80	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.80	1.00	0.031	0.039
D	0.25	0.40	0.010	0.016
E	0.15 REF		0.006 REF	
H	0.00	0.10	0.0000	0.004
J	0.089	0.177	0.0035	0.0070
K	2.30	2.7	0.091	0.106

STYLE 1:
 PIN 1: CATHODE
 2: ANODE